

ABSTRACT OF THE DISCLOSURE

A DRAM cell and a method for fabricating the same are provided. The method includes: forming a trench in a substrate; forming a first capacitor dielectric layer on the surface of the trench; forming a conducting layer inside the trench; forming a second capacitor dielectric layer on the surface of the substrate and on the conducting layer, wherein the substrate around the first and second capacitor dielectric layers serves as a bottom electrode; forming a protruding electrode on the substrate, the protruding electrode being on the substrate around the trench and covering a junction between the trench and the substrate; and electrically connecting the protruding electrode and the conducting layer, the conducting layer and the protruding electrode being an upper electrode.